TOSHIBA Transistor Silicon PNP Triple Diffused Type

# 2SA1940

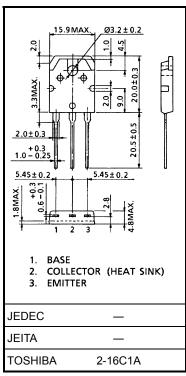
### **Power Amplifier Applications**

Unit: mm

- Complementary to 2SC5197
- Recommended for 55-W high-fidelity audio frequency amplifier output stage

## Maximum Ratings (Tc = 25°C)

| Characteristics             | Symbol           | Rating     | Unit  |  |
|-----------------------------|------------------|------------|-------|--|
| Characteristics             | Cymbol           | rtating    | Offic |  |
| Collector-base voltage      | $V_{CBO}$        | -120       | >     |  |
| Collector-emitter voltage   | V <sub>CEO</sub> | -120       | ٧     |  |
| Emitter-base voltage        | V <sub>EBO</sub> | -5         | V     |  |
| Collector current           | Ic               | -8         | Α     |  |
| Base current                | ΙΒ               | -0.8       | Α     |  |
| Collector power dissipation | D-               | 80         | W     |  |
| (Tc = 25°C)                 | P <sub>C</sub>   | 80         | VV    |  |
| Junction temperature        | Tj               | 150        | °C    |  |
| Storage temperature range   | T <sub>stg</sub> | -55 to 150 | °C    |  |



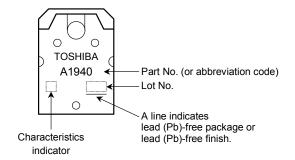
Weight: 4.7 g (typ.)

# **Electrical Characteristics (Tc = 25°C)**

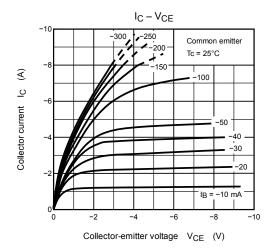
| Characteristics                      | Symbol                     | Test Condition   | Min  | Тур.  | Max  | Unit |
|--------------------------------------|----------------------------|--|------|-------|------|------|
| Collector cut-off current            | I <sub>CBO</sub>           | V <sub>CB</sub> = -120 V, I <sub>E</sub> = 0           | _    | _     | -5.0 | μΑ   |
| Emitter cut-off current              | I <sub>EBO</sub>           | $V_{EB} = -5 \text{ V}, I_C = 0$                       | _    | _     | -5.0 | μΑ   |
| Collector-emitter breakdown voltage  | V (BR) CEO                 | $I_C = -50 \text{ mA}, I_B = 0$                        | -120 | _     | _    | V    |
| DC current gain                      | h <sub>FE (1)</sub> (Note) | V <sub>CE</sub> = -5 V, I <sub>C</sub> = -1 A          | 55   | _     | 160  |      |
|                                      | h <sub>FE (2)</sub>        | V <sub>CE</sub> = -5 V, I <sub>C</sub> = -4 A          | 35   | 75    | _    |      |
| Collector-emitter saturation voltage | V <sub>CE (sat)</sub>      | I <sub>C</sub> = -6 A, I <sub>B</sub> = -0.6 A         | _    | -0.80 | -2.0 | V    |
| Base-emitter voltage                 | V <sub>BE</sub>            | V <sub>CE</sub> = -5 V, I <sub>C</sub> = -4 A          | _    | -0.97 | -1.5 | V    |
| Transition frequency                 | f <sub>T</sub>             | V <sub>CE</sub> = -5 V, I <sub>C</sub> = -1 A          | _    | 30    | _    | MHz  |
| Collector output capacitance         | C <sub>ob</sub>            | V <sub>CB</sub> = -10 V, I <sub>E</sub> = 0, f = 1 MHz | _    | 260   | _    | pF   |

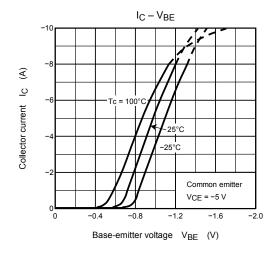
Note: h<sub>FE (1)</sub> classification R: 55 to 110, O: 80 to 160

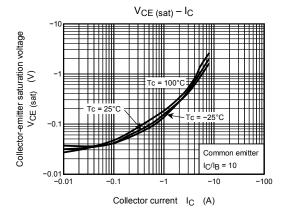
# Marking

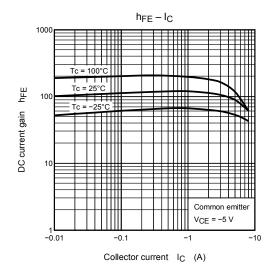


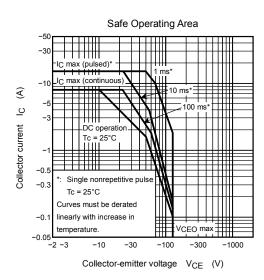
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Handbook" etc..

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